

## LL5711 and LL6263

**V<sub>RRM</sub> : 70V , 60V**

### FEATURES :

- For general purpose applications
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- This diode is also available in the DO-35 case with type designation 1N5711 and 1N6263.
- Pb / RoHS Free

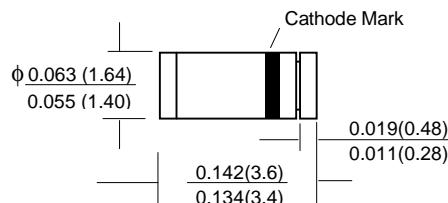
### MECHANICAL DATA :

**Case:** MiniMELF Glass Case (SOD-80C)

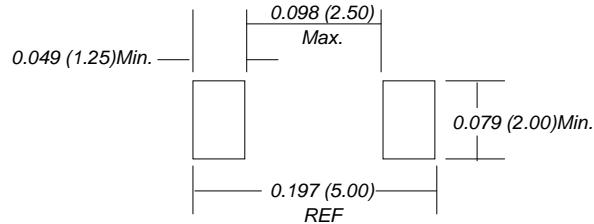
**Weight:** approx. 0.05g

### SCHOTTKY BARRIER DIODES

#### MiniMELF (SOD-80C)



#### Mounting Pad Layout



Dimensions in inches and ( millimeters )

### Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage LL5711 LL6263	V <sub>RRM</sub>	70	V
		60	
Power Dissipation (Infinite Heatsink)	P <sub>D</sub>	400 <sup>(1)</sup>	mW
Maximum Single Cycle Surge 10 µs Square Wave	I <sub>FSM</sub>	2.0	A
Junction Temperature	T <sub>J</sub>	125 <sup>(1)</sup>	°C
Storage temperature range	T <sub>S</sub>	-55 to + 150 <sup>(1)</sup>	°C

### Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage LL5711 LL6263	V <sub>(BR)R</sub>	I <sub>R</sub> = 10 µA	70 60	- -	- -	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 50 V	-	-	200	nA
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> = 1mA I <sub>F</sub> = 15mA	- -	- -	0.41 1.0	V
Diode Capacitance LL5711 LL6263	C <sub>d</sub>	V <sub>R</sub> = 0 V, f = 1MHz	- -	- -	2.0 2.2	pF
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> = 5mA, recover to 0.1I <sub>R</sub>	-	-	1.0	ns

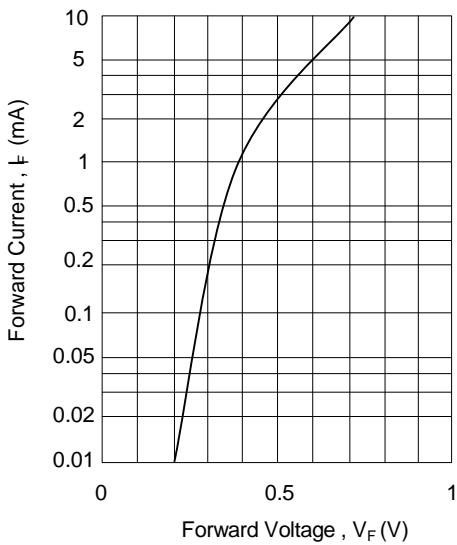
Note: (1) Valid provided that electrodes are kept at ambient temperature



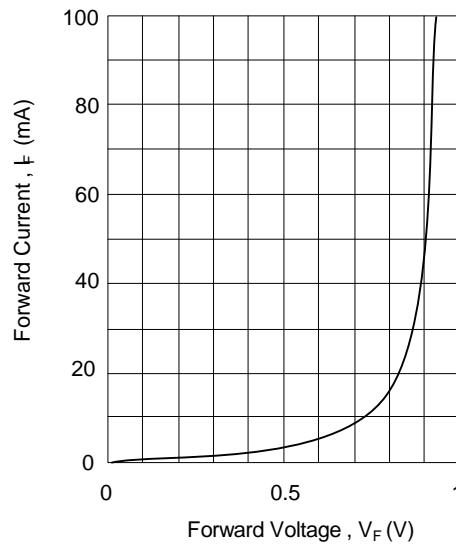
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## RATING AND CHARACTERISTIC CURVES ( LL5711 and LL6263 )

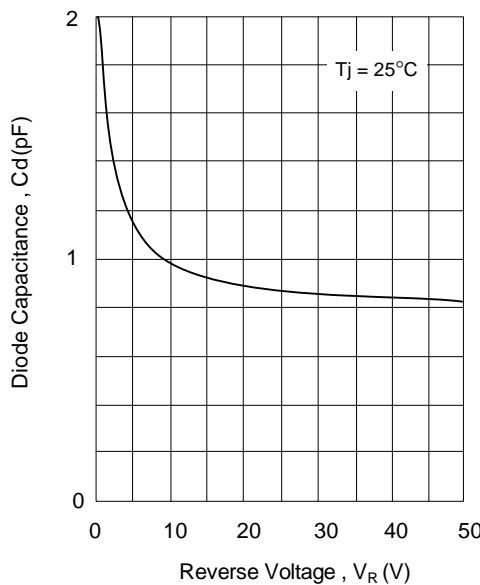
Typical variation of forward current and forward voltage for primary conduction through the schottky barrier



Typical forward conduction curve of combination schottky barrier and PN junction guard ring



Typical capacitance curve as a function of reverse voltage



Typical variation of reverse current at various temperatures

